

## N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (TYP.)
100	0.0260 at V <sub>GS</sub> = 10 V	35	31 nC
	0.0375 at V <sub>GS</sub> = 7 V	31	

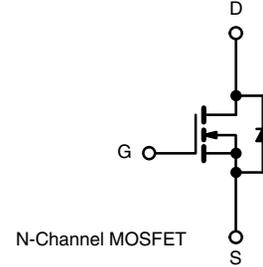
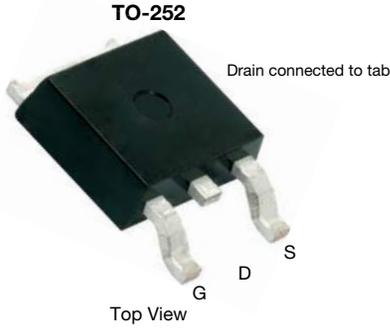
### FEATURES

- TrenchFET® power MOSFET
- 100 % UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### APPLICATIONS

- Primary side switch



### Ordering Information:

SUD35N10-26P-E3 (lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	100	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	35	
		T <sub>C</sub> = 70 °C	32	
		T <sub>A</sub> = 25 °C	12 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	10 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	40	A	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		50 <sup>e</sup>
		T <sub>A</sub> = 25 °C		6.9 <sup>b, c</sup>
Avalanche Current Pulse	I <sub>AS</sub>	33		mJ
Single Pulse Avalanche Energy	E <sub>AS</sub>	55		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	83	
		T <sub>C</sub> = 70 °C	58	
		T <sub>A</sub> = 25 °C	8.3 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	5.8 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	15	18	°C/W	
Maximum Junction-to-Case	R <sub>thJC</sub>	1.5	1.8		

### Notes

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 50 °C/W.
- Calculated based on maximum junction temperature. Package limitation current is 50 A.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	165	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-11	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	-	4.4	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	40	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	-	0.0210	0.0260	Ω
		V <sub>GS</sub> = 7 V, I <sub>D</sub> = 8 A	-	0.0285	0.0375	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 12 A	-	25	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	2000	-	pF
Output Capacitance	C <sub>oss</sub>		-	180	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	60	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	-	31	47	nC
Gate-Source Charge	Q <sub>gs</sub>		-	10	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	9	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	-	1.5	-	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	10	15	ns
Rise Time	t <sub>r</sub>		-	10	15	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	25	
Fall Time	t <sub>f</sub>		-	10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	50	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	40	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 10 A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	50	75	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	100	150	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	38	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	12	-	

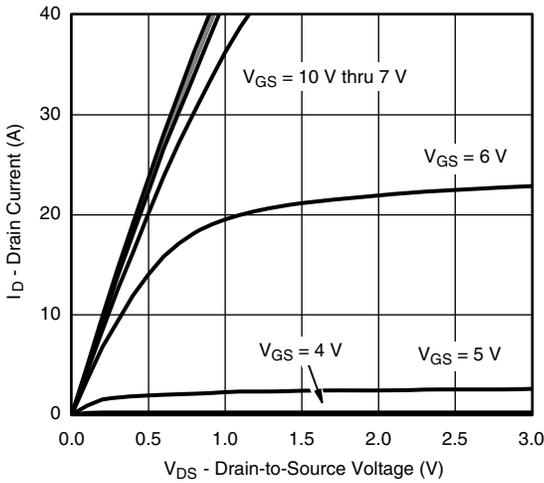
**Note**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

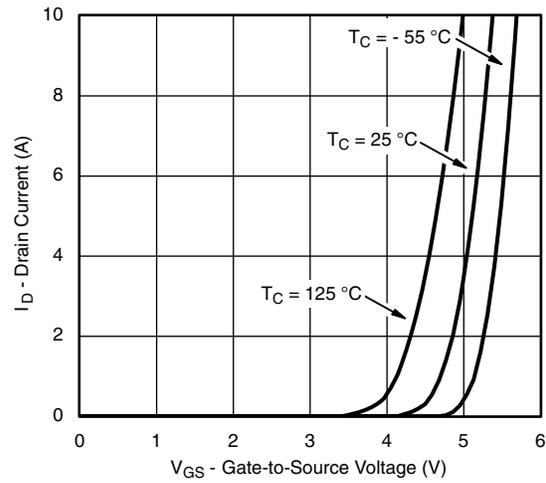
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.



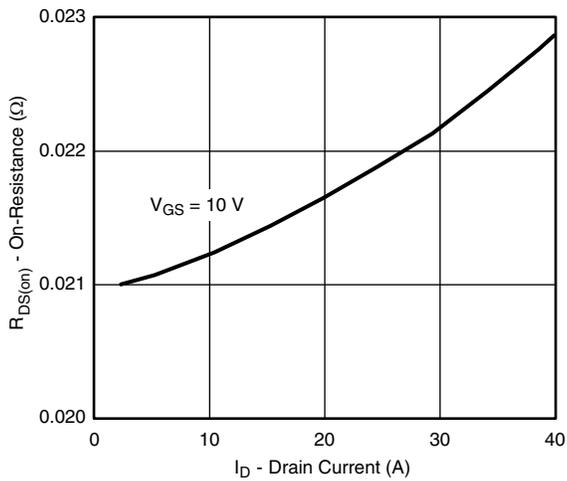
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



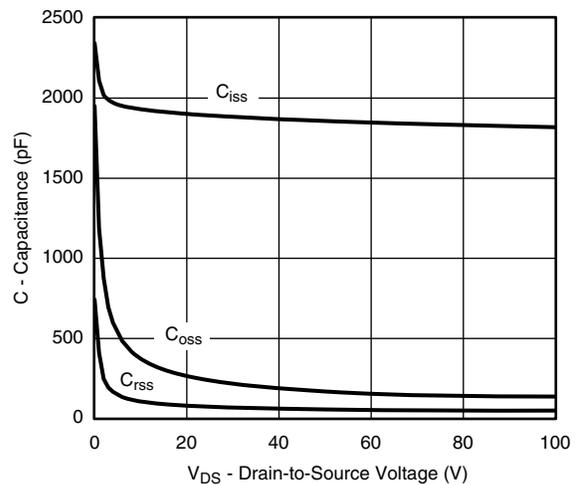
**Output Characteristics**



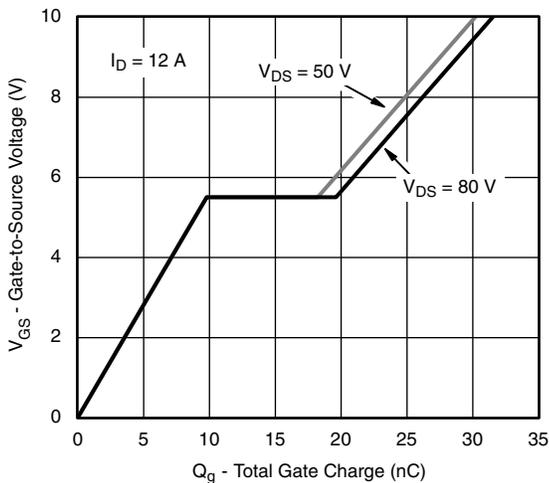
**Transfer Characteristics**



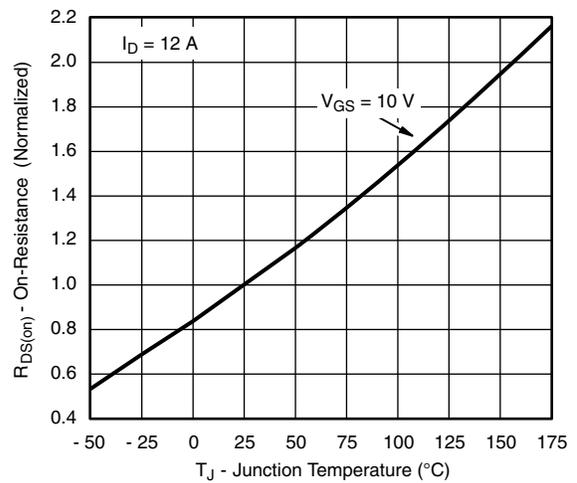
**On-Resistance vs. Drain Current**



**Capacitance**



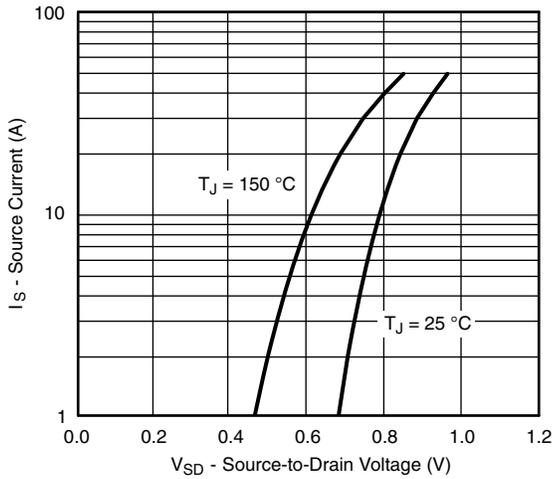
**Gate Charge**



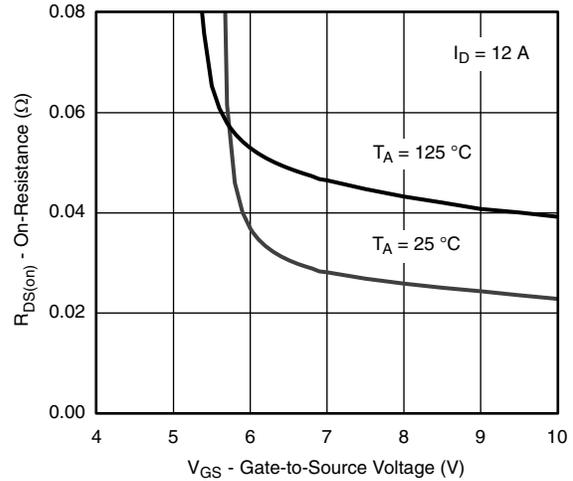
**On-Resistance vs. Junction Temperature**



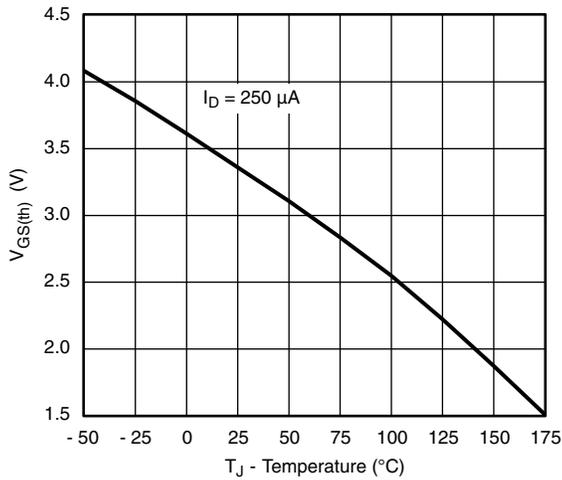
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



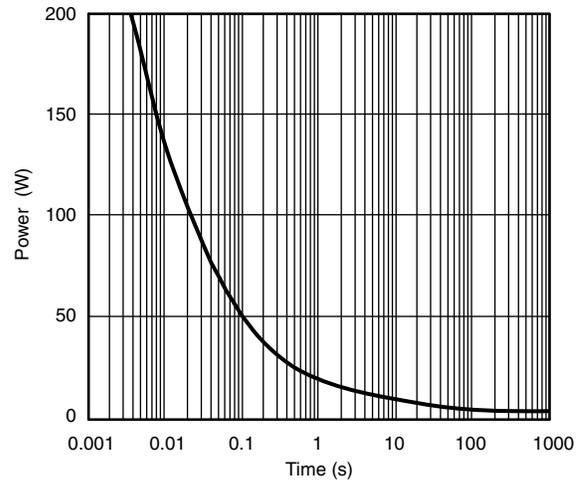
Source-Drain Diode Forward Voltage



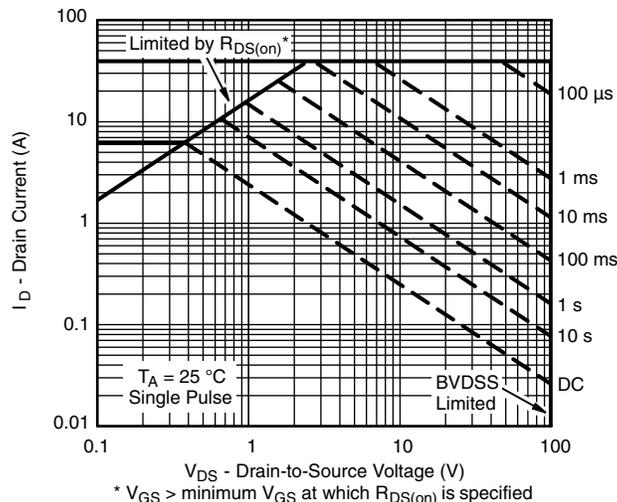
$R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature



Threshold Voltage



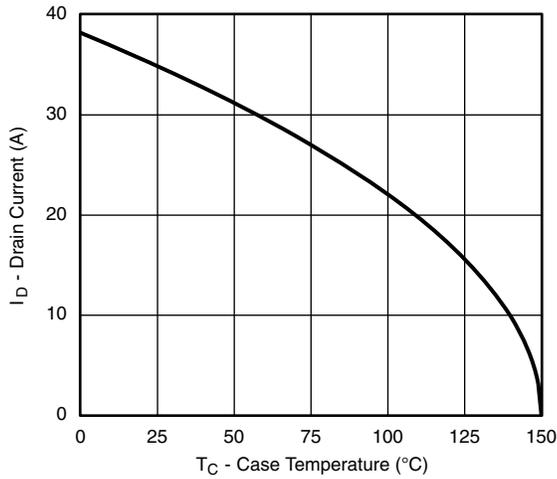
Single Pulse Power, Junction-to-Ambient



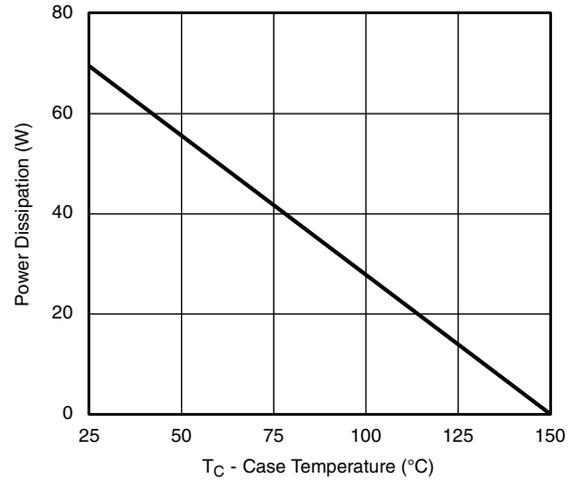
Safe Operating Area



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



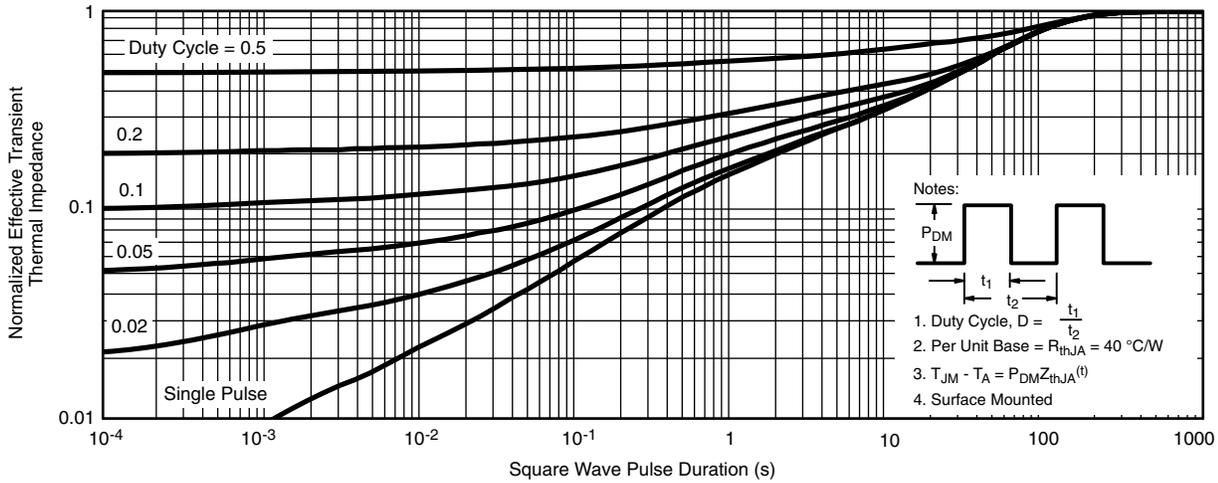
**Power Derating**

**Note**

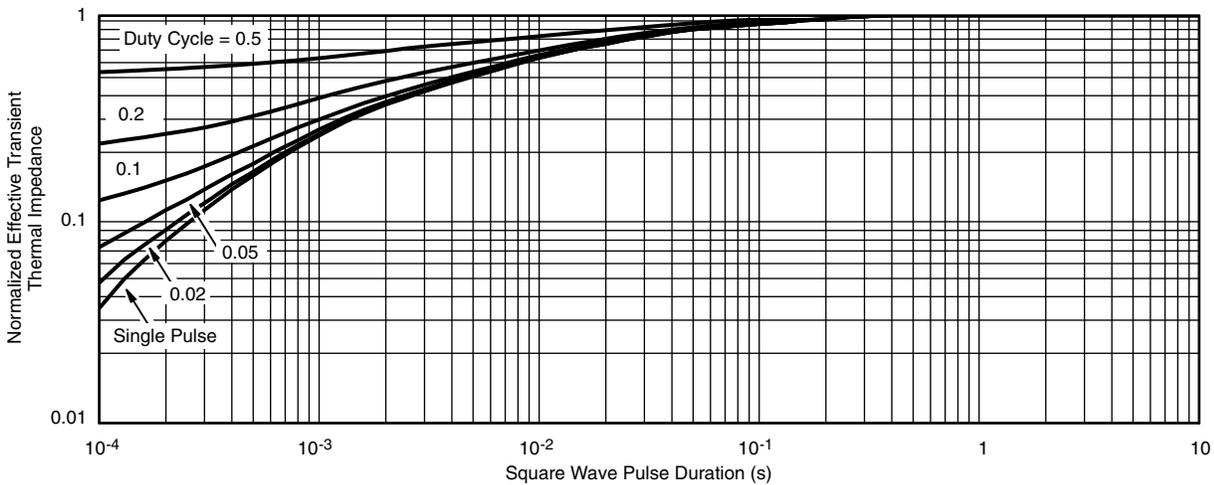
- a. The power dissipation  $P_D$  is based on  $T_J$  (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



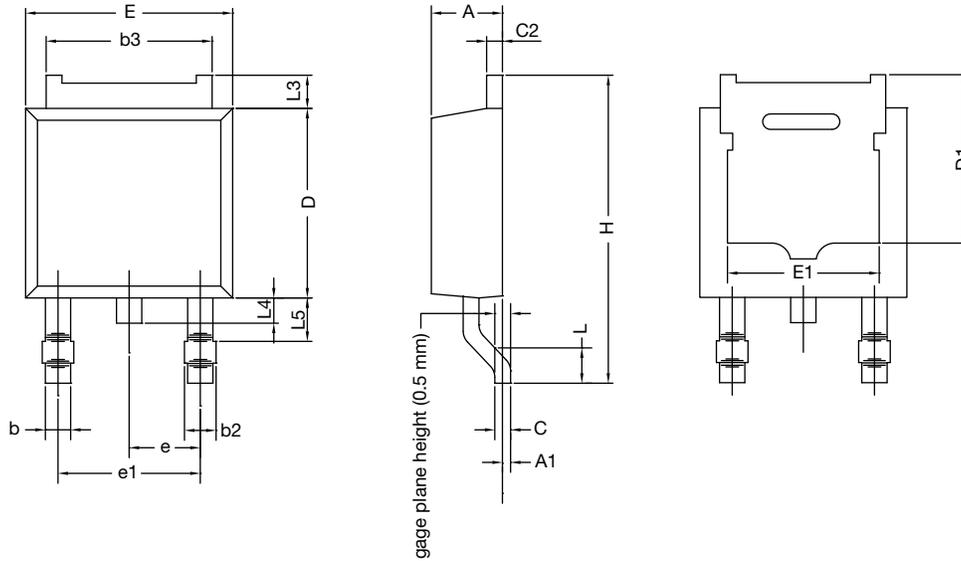
Normalized Thermal Transient Impedance, Junction-to-Case

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# TO-252AA Case Outline

## VERSION 1: FACILITY CODE = Y



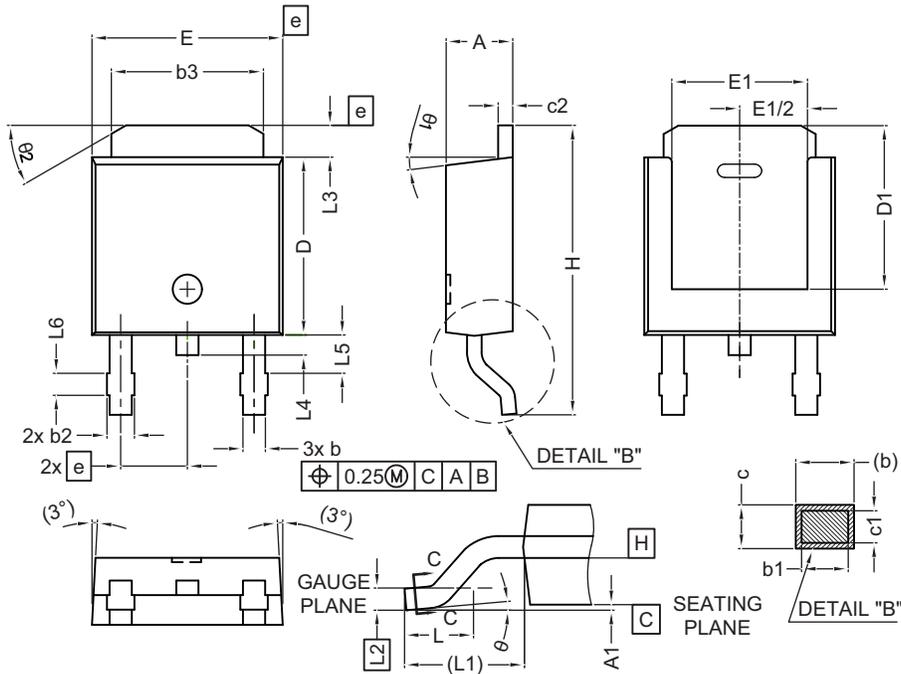
MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

### Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

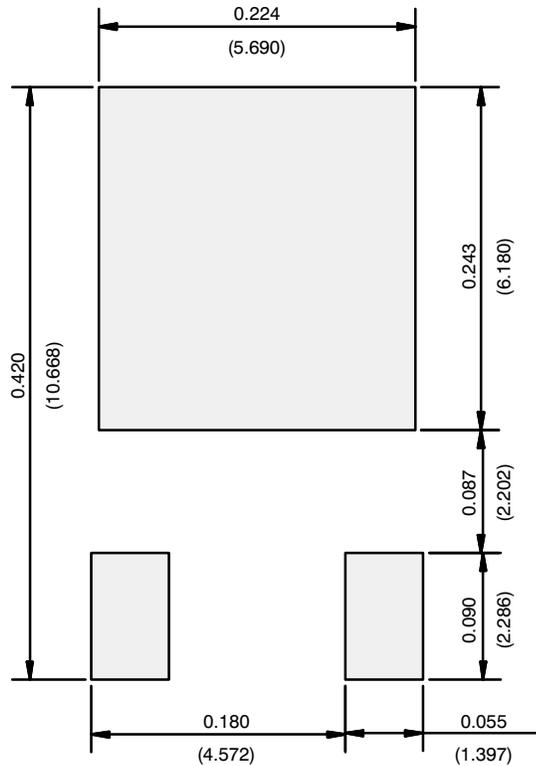
DIM.	MILLIMETERS	
	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022  
 DWG: 5347

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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